

PATENT
Serial No. 10/553,720
Amendment in Reply to Office Action mailed on April 28, 2008

IN THE ABSTRACT

Please delete the current Abstract in its entirety and
substitute therefor the enclosed New Abstract.

NEW ABSTRACT

A photolithographic process includes applying a photoresist layer on a substrate, locally exposing the photoresist layer to a radiation source with a suitable wavelength, providing a suitable liquid developer composition on the substrate, dissolving an exposed or unexposed region of the photoresist layer with the developer composition, rinsing and drying the photoresist layer thereby interrupting the dissolving act. The substrate has a metallic surface in contact with the photoresist layer and the photoresist layer has a thickness $dr < 100$ nm. A relatively high photoresist wall steepness is achieved of 70 degrees or more. The process may be used for the production of high density optical data storage media by using a stamper produced with said process.